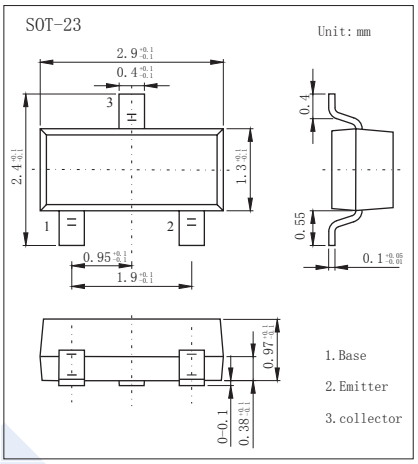
NPN Transistors

2SC3295



■ Features

- Collector Current Capability I_C=150mA
- Collector Emitter Voltage V_{CEO}=50V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	50	V
Collector - Emitter Voltage	V_{CEO}	50	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	150	mA
Base Current	I_B	30	
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	125	℃
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 μA, I_E= 0	50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA, I_B= 0	50			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 μ A, I_C= 0	5			
Collector-base cut-off current	I_{CBO}	V_{CB}= 50V , I_E= 0			0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V , I_C=0			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100 mA, I_B=10mA			0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=100 mA, I_B=10mA			1.2	
DC current gain	h_{FE}	V_{CE}= 6V, I_C= 2mA	600		3600	
Noise figure	NF	V_{CE}= 6V, I_C=0.1mA,f=100Hz,R_G=10KΩ		0.5		dB
		V_{CE}= 6V, I_C=0.1mA,f=1KHz,R_G=10KΩ		0.3		
Collector output capacitance	C_{ob}	V_{CB}= 10V, I_E= 0,f=1MHz		3.5		pF
Transition frequency	f_T	V_{CE}= 10V, I_C=10mA	100			MHz

■ Classification of h_{fe}

Type	2SC3295-A	2SC3295-B
Range	600-1800	1200-3600
Marking	PA	PB

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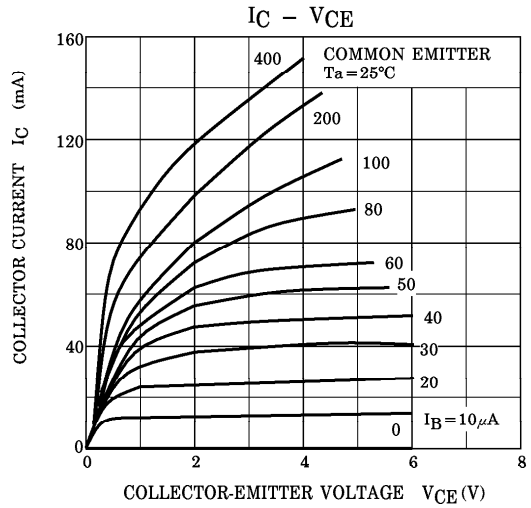
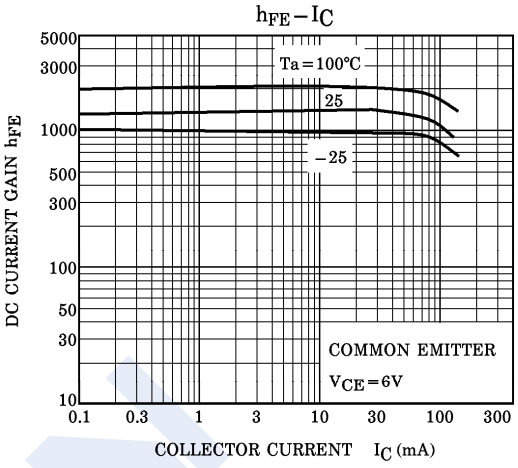
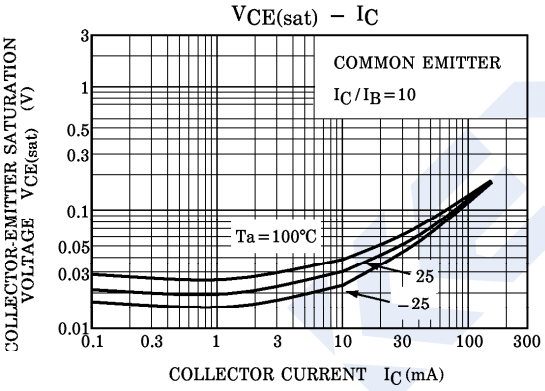
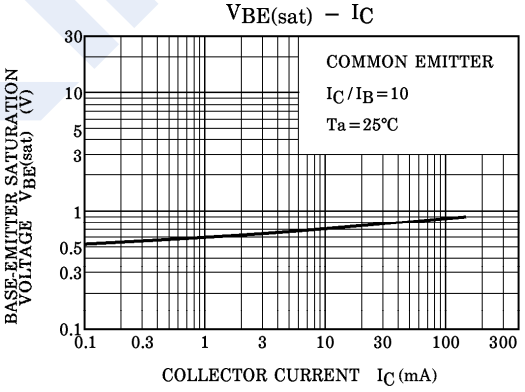
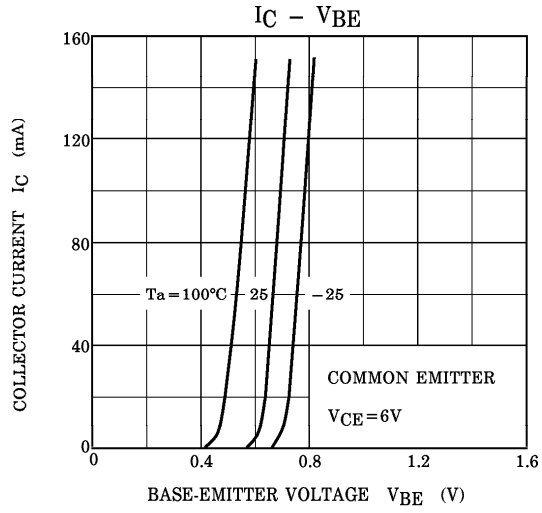
■ Typical Characterisitics

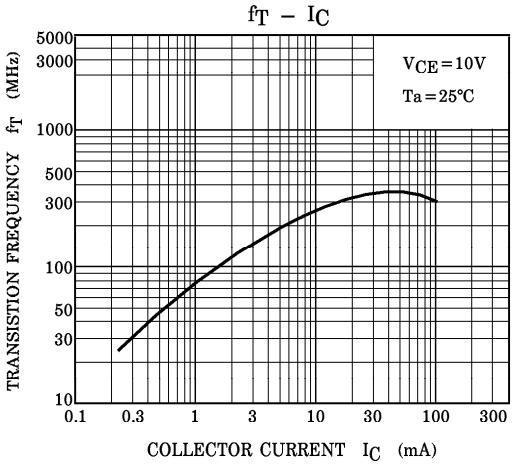












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■ Typical Characterisitics